



Dimensions in mm



Pin3 - Collector

APPLICATIONS

Low Power Silicon Alloy Junction PNP Transistors are specified for use in amplifier circuits.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CB}	Collector – Base Voltage	25V
V_{CE}	Collector – Emitter Voltage	25V
V_{EB}	Emitter – Base Voltage	16V
I_{CM}	Collector Current	100mA
$I_{C(AV)}$	Collector Current ave Over any 20ms	50mA
I_{BM}	Base Current	50mA
$I_{B(AV)}$	Base Currentave Over any 20ms	15mA
I_{EM}	Emitter Current	100mA
$I_{E(AV)}$	Emitter Current ave Over any 20ms	65mA
F_{TOT}	Total Power Dissipation	250mW
T_{STG}, T_J	Operating and Storage Temperature	-53°C to +150°C



ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO} Collector Base Reverse Current	$V_{CB} = 6V$ $I_E = 0$			0.1	μA
	$V_{CB} = 6V$ $I_E = 0$ @100°C			5	
h_{fe} Small Signal Current Gain	$V_{CE} = 6V$ $I_C = 1mA$	25		60	—
f_T Transistion Frequency	$I_C = 1mA$ $V_{CE} = 6V$ $f = 300kc/s$	0.6			μA
NF Noise Figure	$I_C = 0.5mA$ $V_{CE} = 2V$ Z Source = 500 Ω			12	dB
$V_{CE(SAT)}$ Collector-Emitter Saturation Voltage	$I_C = 10mA$ $I_B = 1.5mA$			250	mV
V_{BE} Base Emitter Voltage	$V_{CB} = 5V$ $I_E = 10mA$			750	mV